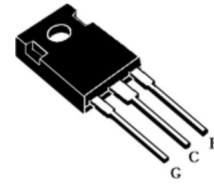


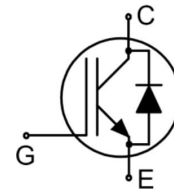
Features

- Low gate charge
- FS Technology
- Short circuit withstand time 10 us
- Saturation voltage: $V_{CE(sat),type}=1.7V$



Applications

- General purpose inverter
- Induction heating(IH)
- UPS



Order Message

| Order codes | Marking | Package |
|-------------|-------------|---------|
| MSG75T65FQC | MSG75T65FQC | TO-247 |

Absolute Ratings($T_c=25^{\circ}C$)

| Parameter | Symbol | Value | Unit |
|---|---------------------------|-----------------|-------------|
| | | MSG75T65FQC | |
| Collector-Emitter Voltage | V_{ce} | 650 | V |
| Collector Current-continuous | $T=25^{\circ}C$ | 150 | A |
| | $T=100^{\circ}C$ | 75 | A |
| Collector Current-pulse (note 1) | I_{CM} | 300 | A |
| Gate-Emitter Voltage | V_{GES} | ± 30 | V |
| Turn-off safe area | - | 75 | A |
| Power Dissipation | PD $T_c=25^{\circ}C$ | 439 | W |
| Operating and Storage Temperature Range | T_J, T_{STG} | $-55 \sim +150$ | $^{\circ}C$ |
| Maximum Lead Temperature for Soldering Purposes | T_L | 300 | $^{\circ}C$ |

1 Diode RMS forward current, $T_c=25^{\circ}C$ 150A $T_c=100^{\circ}C$ 75A

Electrical Characteristics

| Parameter | Symbol | Tests conditions | Min | Typ | Max | Units |
|---|------------------------------|--|-----|------------|----------|--------------|
| Off-Characteristics | | | | | | |
| Collector-Emitter Voltage | BV_{CES} | $I_c=250\mu A, V_{GE}=0V$ | 650 | - | - | V |
| Breakdown Voltage Temperature Coefficient | $\Delta BV_{CES}/\Delta T_J$ | $I_c=0.5mA$, referenced to $25^\circ C$ | - | 0.6 | - | $V/^\circ C$ |
| Zero Gate Voltage Collector Current | I_{CES} | $V_{CE}=650V, V_{GE}=0V$ | - | - | 0.2 | mA |
| Gate-body leakage current, forward | I_{GESF} | $V_{CE}=0V, V_{GE}=20V$ | - | - | 200 | nA |
| Gate-body leakage current, reverse | I_{GESR} | $V_{CE}=0V, V_{GE}=-20V$ | - | - | -200 | nA |
| On-Characteristics | | | | | | |
| Gate Threshold Voltage | $V_{GE(th)}$ | $V_{CE}=V_{GE}, I_c=250\mu A$ | 4.5 | - | 6.5 | V |
| Collector-Emitter saturation Voltage | V_{CESAT} | $V_{GE}=15V, I_c=75A$ $T_c=25^\circ C$ $T_c=150^\circ C$ | - | 1.7 2.0 | 2.2 - | V |
| Short Collector current(Note 2) | $I_{C(SC)}$ | $V_{GE}=15V, V_{CE}=600V$ $t_{sc}<10\mu s, T_c=25^\circ C$ | | 320 | | A |
| Dynamic Characteristics | | | | | | |
| Input capacitance | C_{ies} | $V_{CE}=25V,$ $V_{GE}=0V,$ $f=1.0MHZ$ | - | 5012 | - | pF |
| Output capacitance | C_{oes} | | - | 430 | - | pF |
| Reverse transfer capacitance | C_{res} | | - | 99.6 | - | pF |

Electrical Characteristics

| Parameter | Symbol | Tests conditions | Min | Typ | Max | Units |
|----------------------------------|--------------|---|-----|------|-----|-------|
| Switching Characteristics | | | | | | |
| Turn-on delay time | $t_{d(on)}$ | $V_{CE}=400V, I_c=75A,$ $R_G=7.9\Omega$ $T_c=25^\circ C$ Inductive Load | - | 45 | - | ns |
| Turn-On rise time | t_r | | - | 40 | - | ns |
| Turn-Off delay time | $t_{d(off)}$ | | - | 168 | - | ns |
| Turn-Off Fall time | t_f | | - | 56 | - | ns |
| Turn-on energy | E_{on} | | - | 2.32 | - | mJ |
| Turn-off energy | E_{off} | | - | 0.97 | - | mJ |

MSG75T65FQC

| | | | | | | |
|--|-------------|---|---|------|-----|----|
| Total switching energy | E_{total} | | - | 3.29 | - | mJ |
| Total Gate Charge | Q_g | $V_{CE}=520V,$ $I_C=75A$ $V_{GE}=15V(\text{note } 3,4)$ | - | 27.4 | | nC |
| Anti-Parallel Diode Characteristics and Maximum Ratings | | | | | | |
| Drain-Source Diode Forward Voltage | V_F | $V_{GE}=0V, I_F=75A$ | - | 2.2 | 2.9 | V |
| Diode Reverse recovery time | t_{rr} | $V_{GE}=0V, V_R=400V$ $I_F=75A$ $di/dt=600A/us$ (note 4) | - | 75 | - | ns |
| Reverse recovery charge | Q_{rr} | | - | 664 | - | nC |
| Reverse recovery Current | I_{rr} | | - | 16 | - | A |

Thermal Characteristic

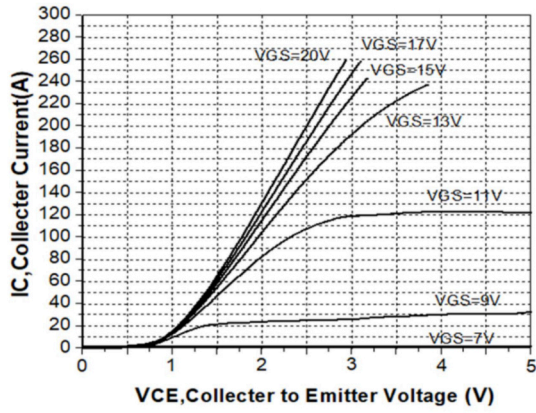
| Parameter | Symbol | Max | Unit |
|---|---------------|------|---------------|
| Thermal Resistance, Junction to Case | $R_{th(j-c)}$ | 0.23 | $^{\circ}C/W$ |
| Thermal Resistance, Junction to Ambient | $R_{th(j-A)}$ | 33 | $^{\circ}C/W$ |

Notes:

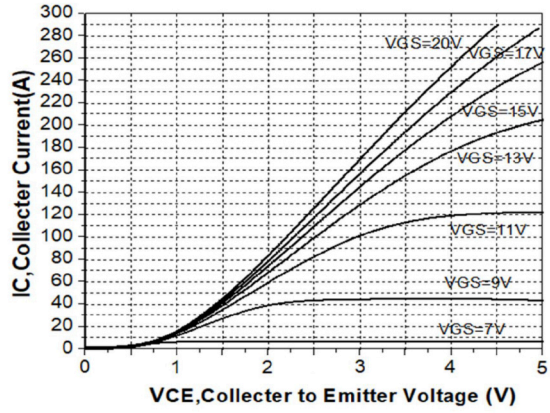
- 1: Pulse width limited by maximum junction temperature
- 2: Allowed number of short circuits:<1000; time between short circuits:>1s.
- 3: Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycles 2%
- 4: Essentially independent of operating temperature

Electrical Characteristics(curves)

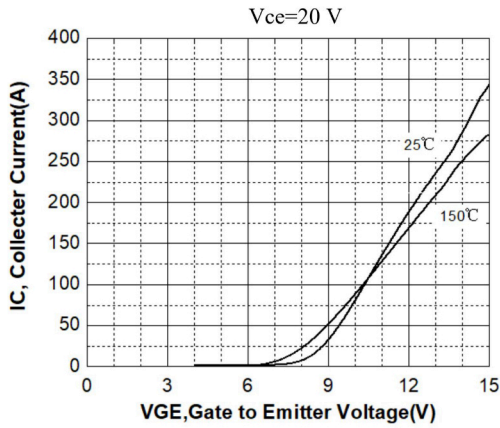
Output Characteristics (25°C)



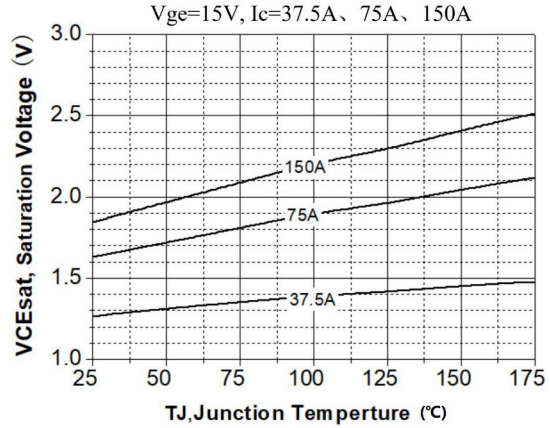
Output Characteristics (150°C)



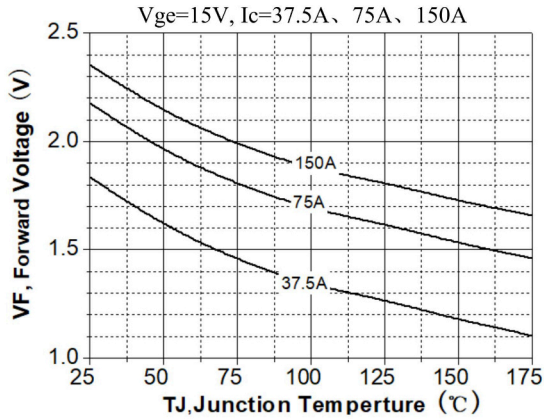
Transfer Characteristics



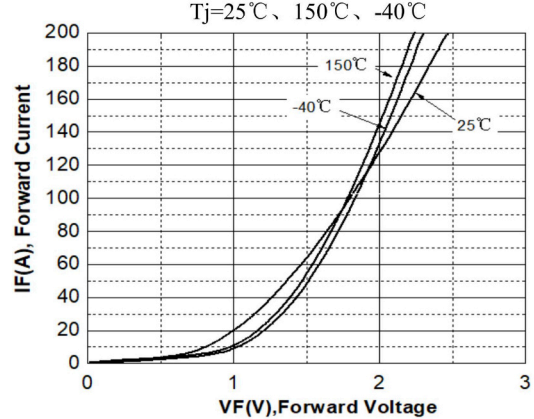
Vcesat vs. Tj



VF vs. Tj

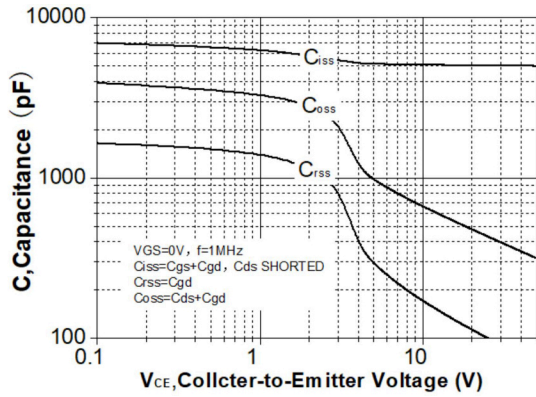


Diode Characteristic



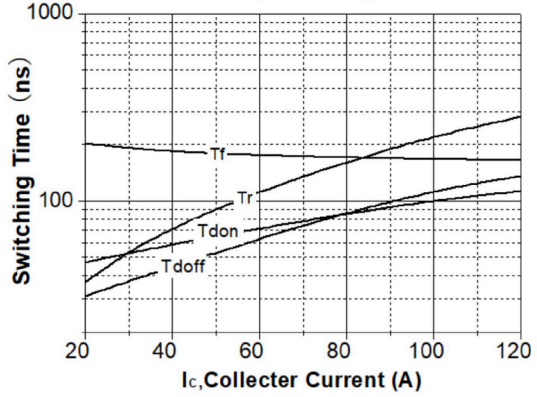
Capacitance Characteristic

Vce=25V, VGE=0V, f=1.0MHz



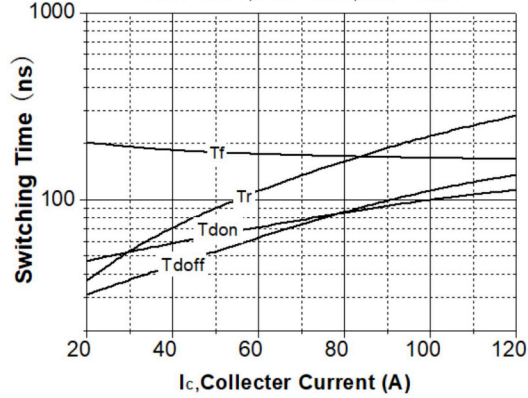
Switching Time vs. IC(25°C)

VCE=400V, VGE=15V, RG=7.9Ω



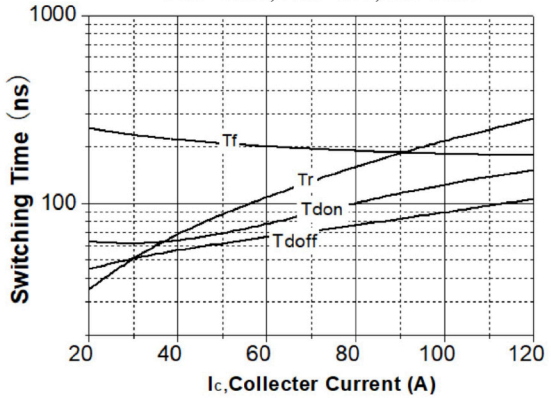
Switching Time vs. IC(25°C)

VCE=400V, VGE=15V, RG=7.9Ω



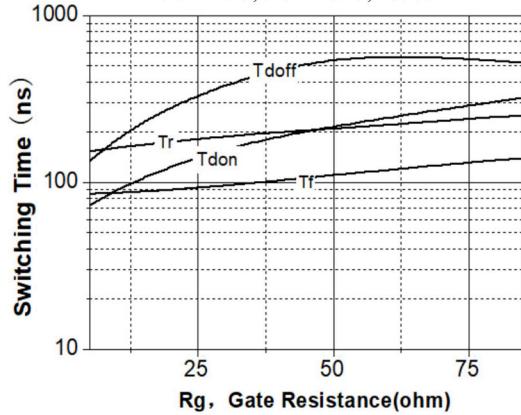
Switching Time vs. IC(150°C)

VCE=400V, VGE=15V, RG=7.9Ω



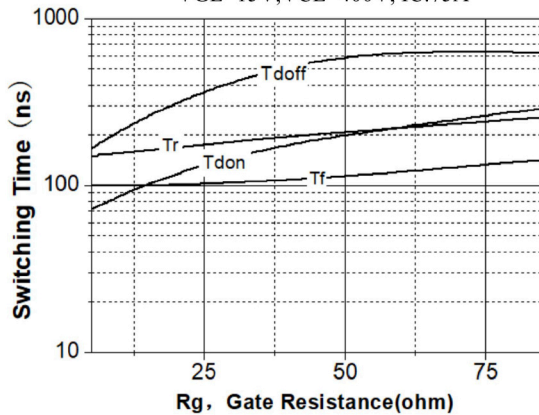
Switching Time vs. Rg(25°C)

VGE=15V, VCE=400V, IC: 75A

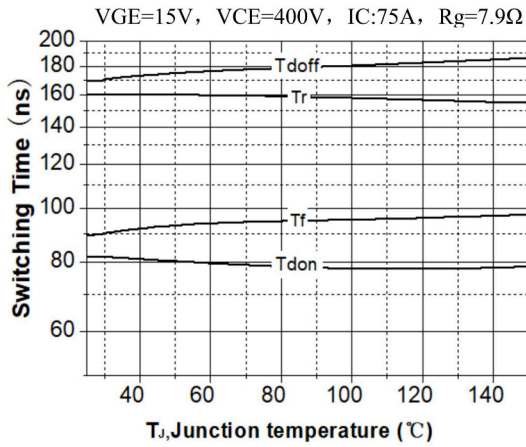


Switching Time vs. Rg(150°C)

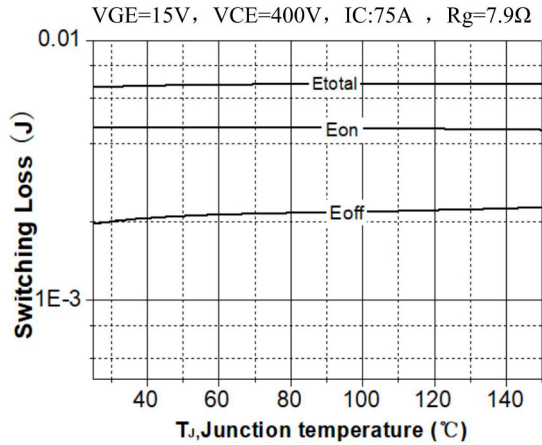
VGE=15V, VCE=400V, IC: 75A



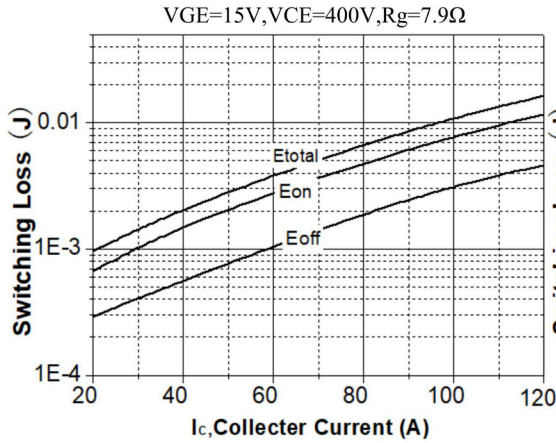
Switching Time vs. Tj



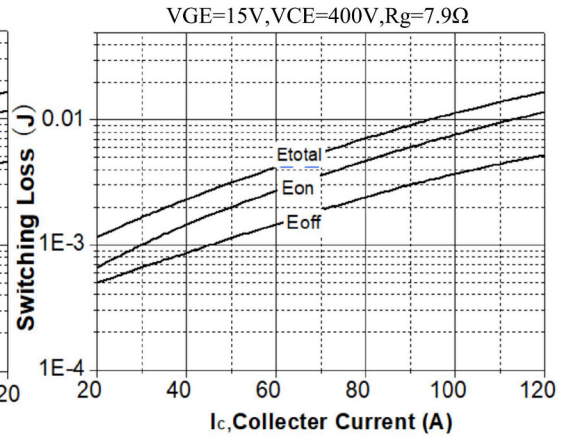
Switching Loss vs. Tj



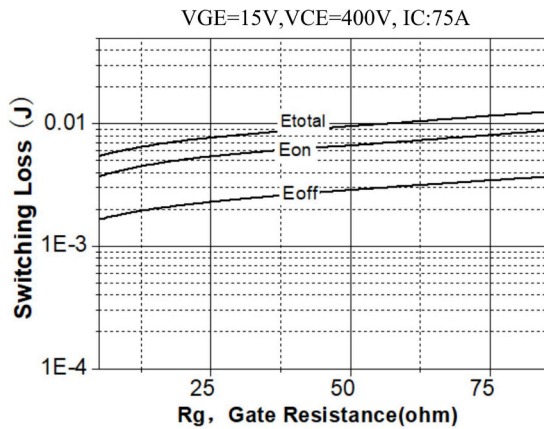
Switching Loss vs. IC(25°C)



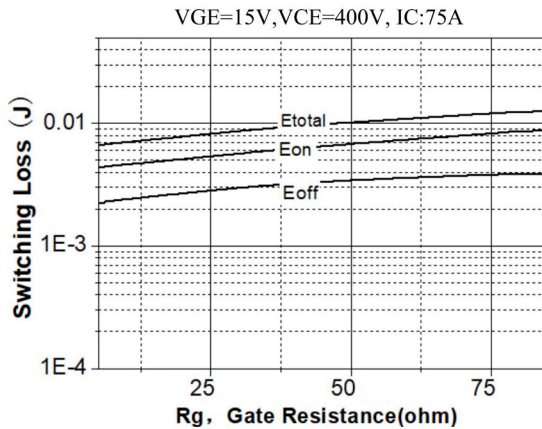
Switching Loss vs. IC(150°C)



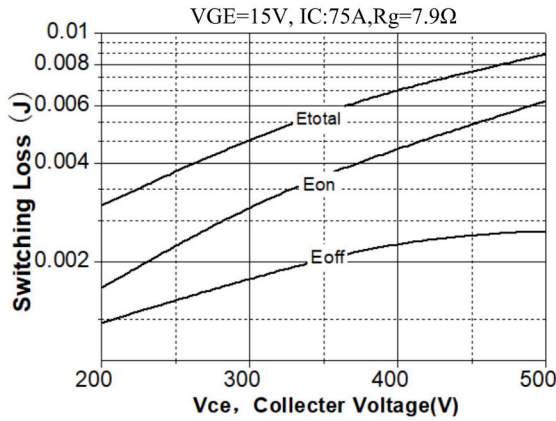
Switching Loss vs. Rg(25°C)



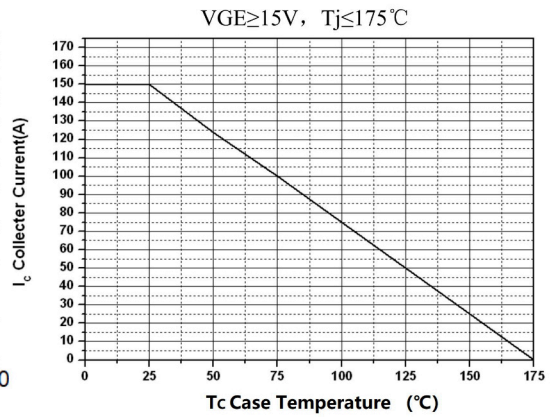
Switching Loss vs. Rg(150°C)



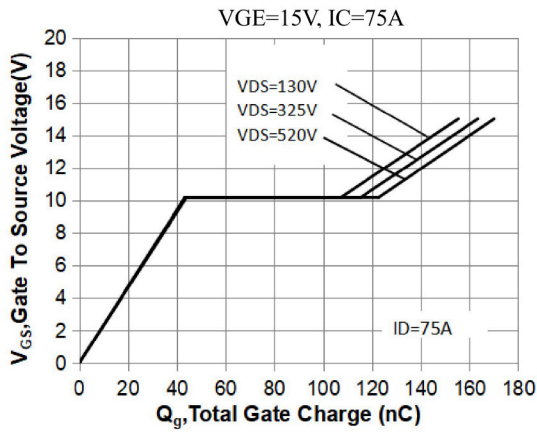
Switching Loss vs. VCE(150°C)



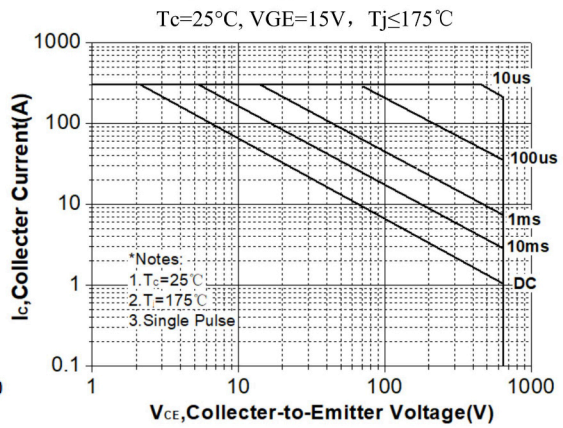
Collector current vs. case temperature



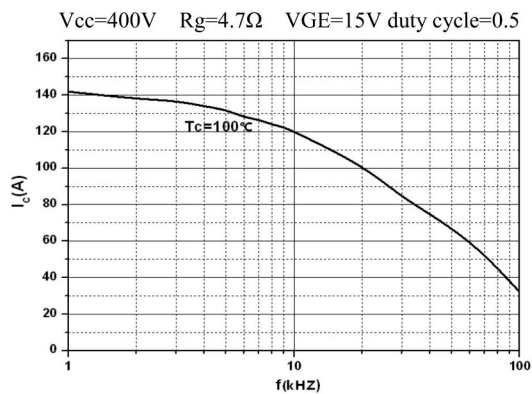
Gate Charge Characteristics



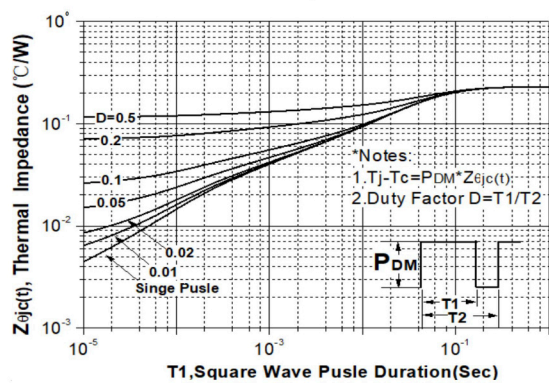
Safe Operating Area For TO-247



Ic vs. f



Transient Thermal Impedance for TO-247



Package Mechanical DATA

